

Silicon NPN Power Transistors

2SD234

DESCRIPTION

- With TO-220 package
- Complement to type 2SB434

APPLICATIONS

- For low frequency power amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

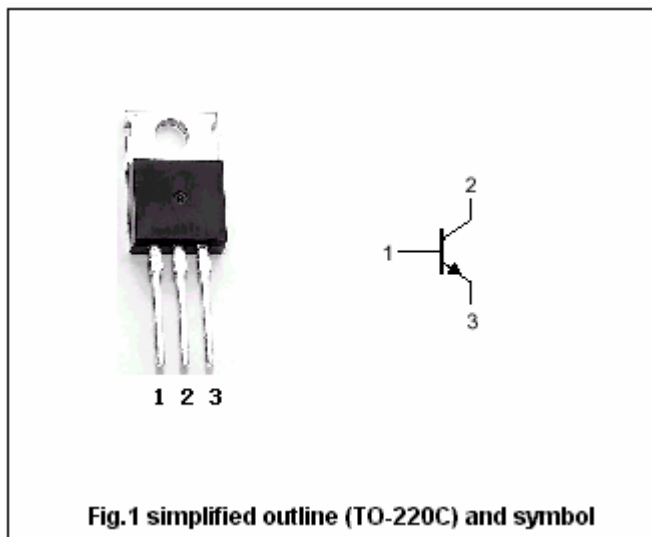


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	50	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
P _C	Collector power dissipation		1.5	W
		T _C =25°C	25	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA, I _B =0	50			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA, I _E =0	60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA, I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A; I _B =0.3A			1.2	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =40V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =0.5A; V _{CE} =1V	40		240	
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V, f=1MHz		90		pF
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V		3		MHz

◆ h_{FE} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

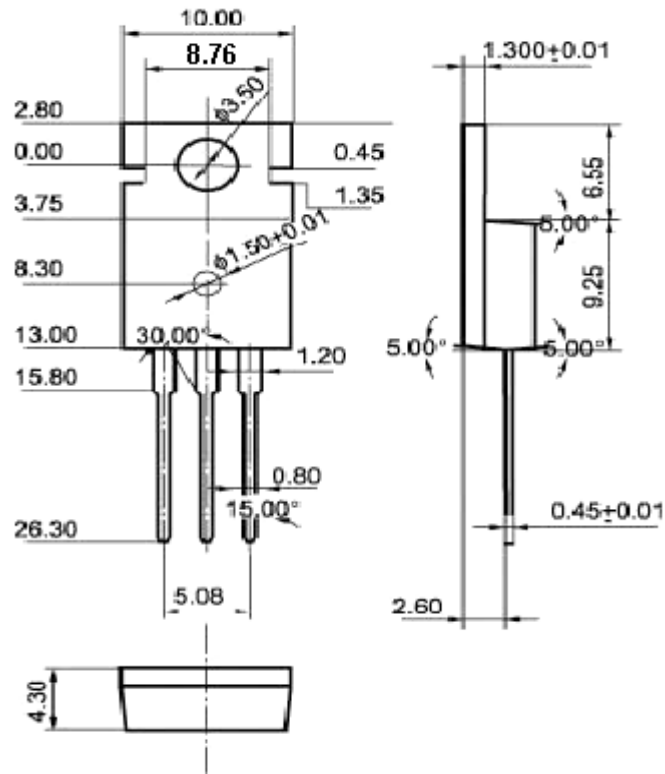


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)